

IN THE CLAIMS

Please use the following claims to replace those of the same number:

- Sub D1*
C1
1. (Twice Amended) A semiconductor device, comprising:
a substrate having circuitry formed therein;
a passivation layer formed overlying at least a portion of the substrate;
a fuse, which may be selectively open-circuited, formed overlying the passivation layer;
and
a packaging material formed in contact with the fuse.
- C2*
11. (Twice Amended) A semiconductor device, comprising:
a substrate having a first circuit formed therein and a second circuit formed therein,
wherein the first circuit has a first contact area and the second circuit has a second contact area;
a passivation layer formed overlying at least a portion of the substrate;
a fuse, which may be selectively open-circuited, formed overlying the passivation layer,
the fuse having a third contact area which is electrically coupled to the first contact area of the first circuit, and the fuse having a fourth contact area which is electrically coupled to the second contact area of the second circuit, wherein the first contact area of the first circuit and the second contact area of the second circuit are no longer electrically connected if the fuse is open-circuited; and
a packaging material formed in contact with the fuse.
- C2*
18. (Twice Amended) A method for forming a semiconductor device having a fuse, comprising:
providing a substrate;
forming a passivation layer overlying at least a portion of the substrate;
forming the fuse overlying the passivation layer; and
forming a packaging material in contact with the fuse.